

PHOTON IS OUR BUSINESS

SPAD (Single Photon Avalanche Diode)



S16835 series

High sensitivity, low noise 1 ch SPAD for visible and near infrared region

S16835 series is a TE-cooled single photon avalanche diode. It is available in types with photosensitivity area of ϕ 54 μ m and ϕ 100 μ m, featuring low dark count and high detection efficiency.

Features

- **■** Single photon counting is possible.
- Low dark count
- Low afterpulses
- Low voltage operation: VBR=40 V typ.
- → High photon detection efficiency: 67% typ.
- ightharpoonup Hgih gain: 10^6 to 10^7 typ.

Applications

- **Low-light-level measurement**
- **■** Particle diameter measurement
- **⇒** Fluorescence measurement
- → Analytical instrument

Structure

Parameter	S16835-050DG	S16835-100DG	Unit
Effective photosensitive area	ф54	ф100	μm
Number of pixel	1		-
Package	TO-8		
Window	Borosilicate glass		
Refractive index of window material	1.52		
Cooling	Two-stage TE-cooling		

■ Absolute maximum ratings (unles otherwise noted Ta=25 °C)

Parameter	Symbol	S16835-050DG	S16835-100DG	Unit
Operating temperature*1	Topr	-20 to +60		°C
Storage temperature*1	Tstg	-20 to +85		°C
Chip temperature	Tchip	-25 to ambient temperature		°C
Thermistor power dissipation	Pd_th	0.2		mW
TE-cooler allowable current	ITE max	1		A
TE-cooler allowable voltage	VTE max	0.9		V

^{*1:} No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environments, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliablity.

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

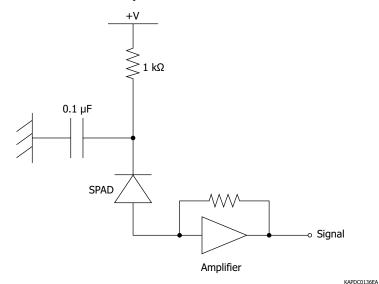
■ Elctrical and optical characteristics (Typ. Ta=25 °C, Tchip=-20 °C, unles otherwise noted)

Parameter		Symbol	Condition	S16835-050DG	S16835-100DG	Unit
Spectral response range	ge λ 400 to 1000		1000	nm		
Peak sensitivity wavelen	gth	λр		610		nm
Photon detection efficier	ncy*2	PDE	λ=λp, VR=Vop	67		%
Dark Countrate F	Тур.	DCR	VR=Vop	0.015	0.06	kcps
	Max.			0.05	0.2	
Terminal capacitance		Ct	VR=Vop, f=100 kHz	2.8	3.2	pF
Gain		М	VR=Vop	6.0×10^{6}	1.5×10^{7}	-
Breakdown voltage		VBR		40 ± 5		V
Recommended operation	n voltage* ³	Vop		VBR + 7		V
Temperature coefficient at recommended operation voltage		ΔTVop		45		mV/°C
Recommended TE-cooler temperature TTE		TTE_recom		-20		°C

^{*2:} Photon detection efficiency includes afterpulses.

Note: The above characteristics were measured at the operating voltage that yields the lested gain (See the data attached to each product).

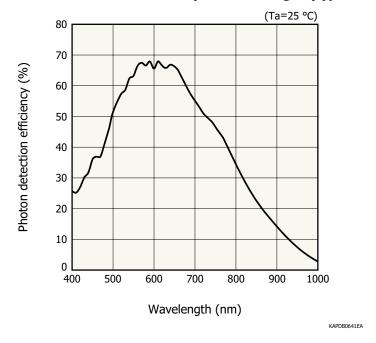
- Connection example





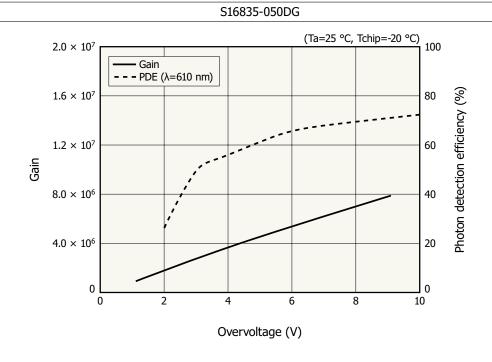
^{*3:} Refer to the data provided with the product.

Photon detection efficiency vs. wavelength (typical example)



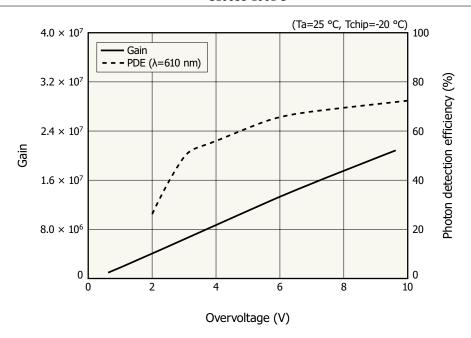
Photon detection efficiency include afterpulses.

⇒ Gain, photon detection efficiency vs. overvoltage characteristics (typical example)



KAPDB0639E

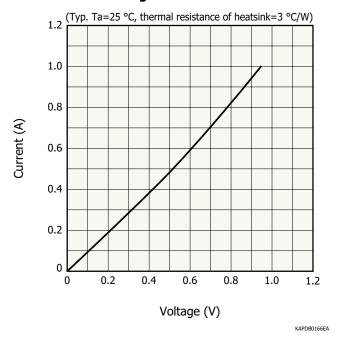
S16835-100DG



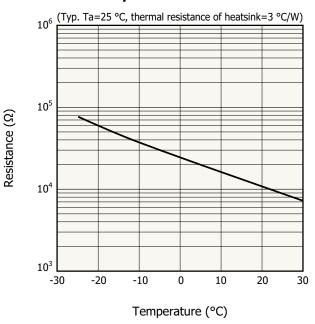
KAPDB0640EA

SPAD characteristics vary with the operating voltage. Although increasing the operating voltage improves the photon detection efficiency and time resolution, it also increases the dark count at the same time, so an optimum operating voltage must be selected to match the application.

Current vs. voltage characteristics of TE-cooler

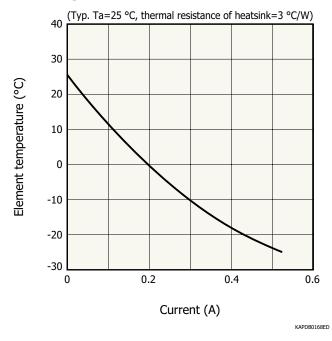


Thermistor temperature characteristics

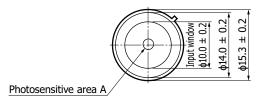


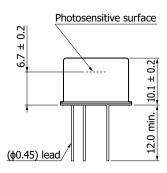
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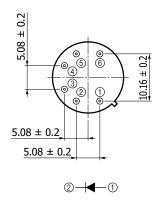
- Cooling characteristics of TE-cooler



Dimensional outlines (unit: mm)







Type no.	Α	
S16835-050DG	φ54 μm	
S16835-100DG	φ100 μm	

Tolerance unless otherwise noted: ± 0.2 Distance from photosensitive area center to cap center $-0.3 \le X \le +0.3$ $-0.3 \le Y \le +0.3$

- ① Detector (anode)
- 2 Detector (cathode)
- ③TE-cooler (-)
- 4 TE-cooler (+)
- 56 Thermistor

KAPDA0228EA

Recommended soldering conditions

· Solder temperature: 260 °C (10 s or less, once)

Note: When you set soldering conditions, check that problems do not occur in the product by testing out the conditions in advance.

Precautions

■ Electrostatic breakdown

The S16835 series may be destroyed or deteriorated by static electricity. See precautions of "metal, ceramic, plastic package products" for use.

■ Wiring

If necessary, incorporate an appropriate protective circuit in a power supply, device, and measuring instrument, etc. to prevent overvoltage and overcurrent.

Related product

SPAD module C16531 series, C16533-050GD, C16534-050GD

These are photon counting modules capable of detecting low-level-light. They consist of a TE-cooled SPAD, amplifier, comparator, SPAD bias circuit, and temperature control circuit. These modules are operated by simply supplying external power (±5 V). Fiber coupling types and compact and lightweight modules suitable for integration into devices are also available.

Type no.	Output format	Built-in element	Photosensitive area (µm)	Note
C16531-050GD	- Digital	S16835-050DG	ф54	
C16531-100GD		S16835-100DG	φ100	
C16533-050GD		S16835-050DG	ф54	Fiber coupling type
C16534-050GD		S16835-050DG	φ54	Fiber coupling type (for embedded use)







C16531-050GD/-100GD

C16533-050GD

C16534-050GD

Related information

www.hamamatsu.com/sp/ssd/doc en.html

- Precautions
- · Disclaimer
- · Metal, ceramic, plastic package products

Information described in this material is current as of July 2024.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use. Copying or reprinting the contents described in this material in whole or in part is prohibited without our prior permission.

MAMATSU

www.hamamatsu.com

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Chuo-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81)53-434-3311, Fax: (81)53-434-5184

ILIZO-I ICRINIO-CRO, CRUO-KU, Hamamatsu Cuty, 435-858 Japan, Ielephone: (81)53-434-3311, Fax: (81)53-434-5184

U.S.A.: HAMAMATSU CORPORATION: 360 Foothill Road, Bridgewater, NJ 08807, U.S.A., Telephone: (1)908-231-0960, Fax: (1)908-231-1218

Germany: HAMAMATSU PHOTONICS DEUTSCHLAND GMBH: Arzbergerstr. 10, 82211 Herrsching am Ammersee, Germany, Telephone: (49)8152-375-0, Fax: (49)8152-265-8 E-mail: info@hamamatsu.de

France: HAMAMATSU PHOTONICS FRANCE S.A.R.L.: 19 Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: (33)1 69 53 71 00, Fax: (33)1 69 53 71 10, Fax: (31)1 69 53 71 10, Fax: (31)1 69 53 71 00, Fax: (32)1 60 53 71 00, Fax: (32)1 60 53 71 00, Fax: (32)1 6